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a region in the substrate for collecting but not storing carriers;
at least one doped or inverted region of a first conductivity in or on the substrate; and
a least one planar current flow, carrier transport pathway from or through the carrier
collecting region to the at least one doped or inverted region, in which carrier transport
pathway carriers are not stored.

6. (Amended) The pixel structure according to claim 1, wherein the region for collecting but
not storing carriers is substrate under a polysilicon cover layer.

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7. (Amended) The pixel structure according to claim 1, wherein the region for collecting but
not storing carriers is diffusion limited.

8. (Amended) The pixel structure according to claim 1, further comprising at least one
implant confining the region for collecting but not storing carriers along at least one
dimension thereof.

9. (Amended) The pixel structure according to claim 1, further comprising regions of a
second conductivity type in or on the substrate avoiding touching of the region for collecting
but not storing carriers and a field oxide.
